The A881B fast recovery diode is designed as parallel mate for 3000A I_{RON} GTO’s used in voltage fed inverter circuits normally requiring the bypass function. Its relatively low recovery current and charge in combination with low thermal resistance offer an advantage for optimizing other circuit components. It is manufactured by the proven multi-diffusion process with 77mm diameter silicon and is supplied in a disc-type package ready to mount using commercially available heat dissipators and clamping hardware.